

**Silicon NPN Power Transistors**

**BU536**

**DESCRIPTION**

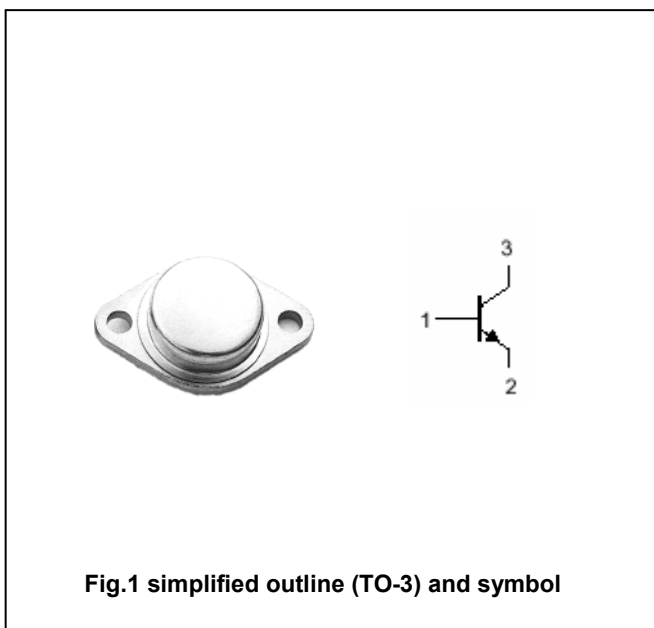
- With TO-3 package
- High voltage
- Fast switching speed

**APPLICATIONS**

- For color TV horizontal deflection circuits.

**PINNING(see fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



**Fig.1 simplified outline (TO-3) and symbol**

**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1100	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	480	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		8	A
I <sub>CM</sub>	Collector current-peak	t <sub>p</sub> <5ms	15	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> =25□	62	W
T <sub>j</sub>	Junction temperature		175	□
T <sub>stg</sub>	Storage temperature		-65~175	□

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance junction to case	1.0	□/W

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA; I <sub>B</sub> =0;	480			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =10mA; I <sub>C</sub> =0;	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.8A			5.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.8A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =1100V; I <sub>E</sub> =0			1.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			0.1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	10			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =4A ; V <sub>CE</sub> =5V	6.5			

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PACKAGE OUTLINE

